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FDMS1D5N03

N-Channel PowerTrench® MOSFET 30 V, 218 A, 1.15 mΩ

Features

- Max $r_{DS(on)}$ = 1.15 mΩ at V_{GS} = 10 V, I_D = 40 A
- Max $r_{DS(on)}$ = 1.3 mΩ at V_{GS} = 4.5 V, I_D = 37 A
- Advanced Package and Silicon Combination for Low $r_{DS(on)}$ and High Efficiency
- MSL1 Robust Package Design
- 100% UIL Tested
- RoHS Compliant

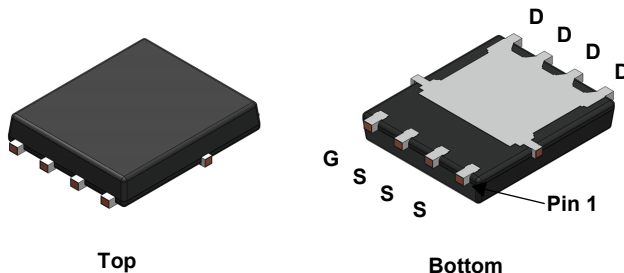


General Description

This N-Channel MOSFET has been designed specifically to improve the overall efficiency and to minimize switch node ringing of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge and extremely low $r_{DS(on)}$.

Applications

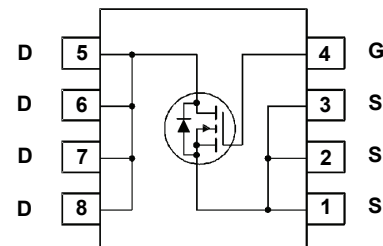
- OringFET
- Synchronous Rectifier



Top

Bottom

Power 56



MOSFET Maximum Ratings $T_A = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Ratings	Units
V_{DS}	Drain to Source Voltage	30	V
V_{GS}	Gate to Source Voltage	± 16	V
I_D	Drain Current -Continuous $T_C = 25^\circ\text{C}$ (Note 5)	218	A
	-Continuous $T_C = 100^\circ\text{C}$ (Note 5)	138	
	-Continuous $T_A = 25^\circ\text{C}$ (Note 1a)	40	
	-Pulsed (Note 4)	1084	
E_{AS}	Single Pulse Avalanche Energy (Note 3)	600	mJ
P_D	Power Dissipation $T_C = 25^\circ\text{C}$	83	W
	Power Dissipation $T_A = 25^\circ\text{C}$ (Note 1a)	2.5	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +150	$^\circ\text{C}$

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case	1.5	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDMS1D5N03	FDMS1D5N03	Power 56	13 "	12 mm	3000 units

Electrical Characteristics $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
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Off Characteristics

BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$, $V_{GS} = 0\text{ V}$	30			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^{\circ}\text{C}$		14		mV/ $^{\circ}\text{C}$
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24\text{ V}$, $V_{GS} = 0\text{ V}$			1	μA
I_{GSS}	Gate to Source Leakage Current	$V_{GS} = \pm 16\text{ V}$, $V_{DS} = 0\text{ V}$			± 100	nA

On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$, $I_D = 250\text{ }\mu\text{A}$	0.8	1.1	2.0	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$, referenced to $25\text{ }^{\circ}\text{C}$		-4		mV/ $^{\circ}\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}$, $I_D = 40\text{ A}$		0.9	1.15	m Ω
		$V_{GS} = 4.5\text{ V}$, $I_D = 37\text{ A}$		1.0	1.3	
		$V_{GS} = 10\text{ V}$, $I_D = 40\text{ A}$, $T_J = 125\text{ }^{\circ}\text{C}$		1.3	1.6	
g_{FS}	Forward Transconductance	$V_{DS} = 5\text{ V}$, $I_D = 40\text{ A}$		320		S

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{DS} = 15\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$		6920	9690	pF
C_{oss}	Output Capacitance			1700	2380	pF
C_{rss}	Reverse Transfer Capacitance			90	150	pF
R_g	Gate Resistance		0.1	0.5	1.5	Ω

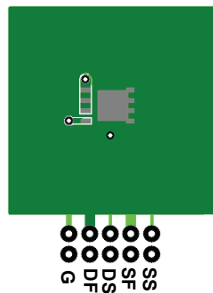
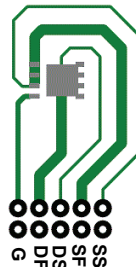
Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 15\text{ V}$, $I_D = 40\text{ A}$, $V_{GS} = 10\text{ V}$, $R_{GEN} = 6\text{ }\Omega$		16	29	ns
t_r	Rise Time			5	10	ns
$t_{d(off)}$	Turn-Off Delay Time			52	84	ns
t_f	Fall Time			4	10	ns
Q_g	Total Gate Charge	$V_{GS} = 0\text{ V to } 10\text{ V}$	$V_{DD} = 15\text{ V}$, $I_D = 40\text{ A}$	99	139	nC
Q_g	Total Gate Charge	$V_{GS} = 0\text{ V to } 4.5\text{ V}$		45	63	nC
Q_{gs}	Gate to Source Charge			13		nC
Q_{gd}	Gate to Drain "Miller" Charge			7.8		nC

Drain-Source Diode Characteristics

V_{SD}	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$, $I_S = 2.1\text{ A}$ (Note 2)		0.7	1.2	V
		$V_{GS} = 0\text{ V}$, $I_S = 40\text{ A}$ (Note 2)		0.8	1.3	
t_{rr}	Reverse Recovery Time	$I_F = 40\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$		51	82	ns
Q_{rr}	Reverse Recovery Charge			39	62	nC

Notes:

1. $R_{\theta JA}$ is determined with the device mounted on a 1 in² pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material.a) 50 $^{\circ}\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copperb) 125 $^{\circ}\text{C}/\text{W}$ when mounted on a minimum pad of 2 oz copper.2. Pulse Test: Pulse Width < 300 μs , Duty cycle < 2.0%.3. E_{AS} of 600 mJ is based on starting $T_J = 25\text{ }^{\circ}\text{C}$, $L = 3\text{ mH}$, $I_{AS} = 20\text{ A}$, $V_{DD} = 30\text{ V}$, $V_{GS} = 10\text{ V}$. 100% tested at $L = 0.1\text{ mH}$, $I_{AS} = 63\text{ A}$ 4. Pulse I_d please refer to Fig.11 SOA curve for detail.

5. Computed continuous current limited to Max Junction Temperature only, actual continuous current will be limited by thermal & electro-mechanical application board design.

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted.

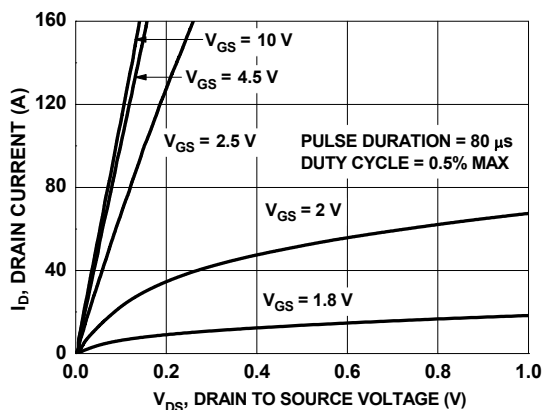


Figure 1. On Region Characteristics

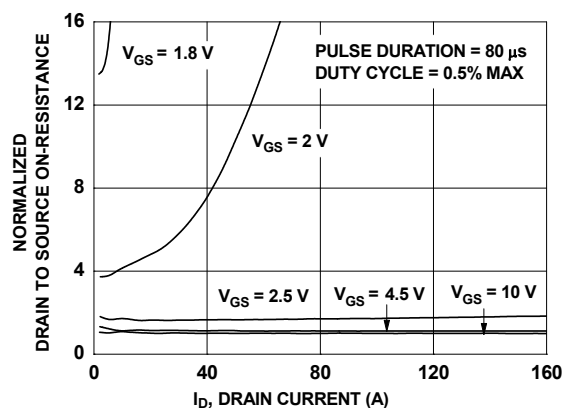


Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage

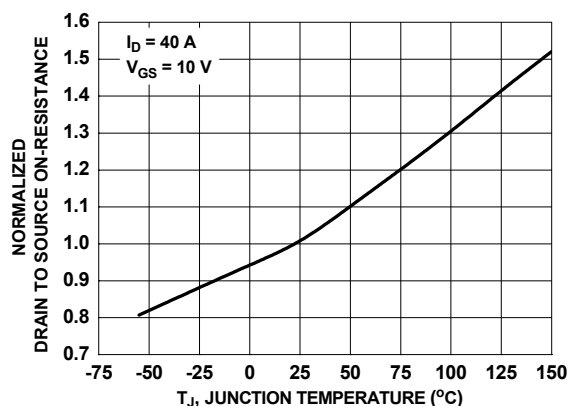


Figure 3. Normalized On Resistance vs. Junction Temperature

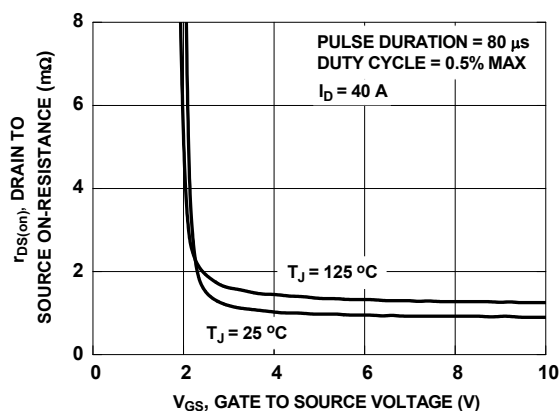


Figure 4. On-Resistance vs. Gate to Source Voltage

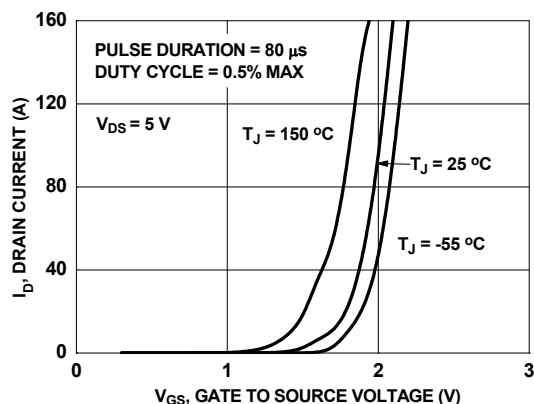


Figure 5. Transfer Characteristics

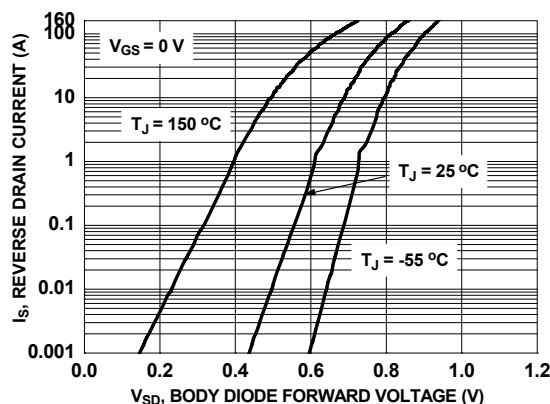


Figure 6. Source to Drain Diode Forward Voltage vs. Source Current

Typical Characteristics $T_J = 25^\circ\text{C}$ unless otherwise noted.

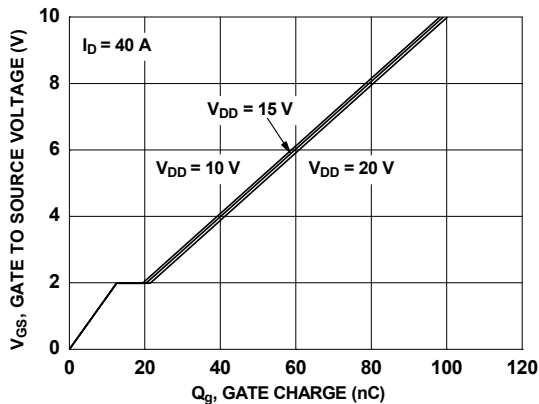


Figure 7. Gate Charge Characteristics

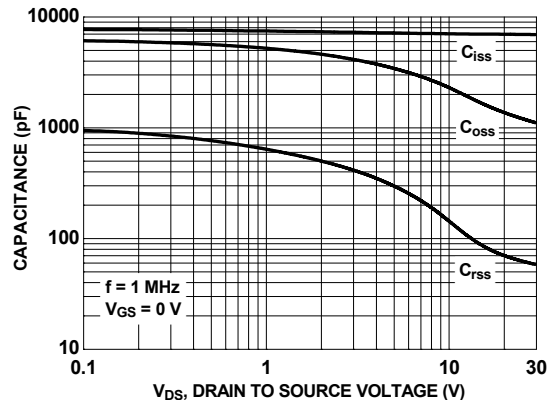


Figure 8. Capacitance vs. Drain to Source Voltage

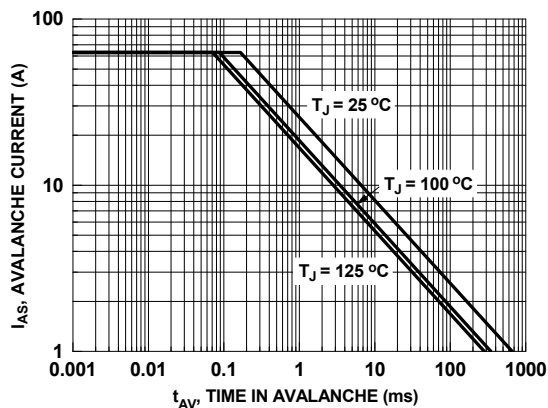


Figure 9. Unclamped Inductive Switching Capability

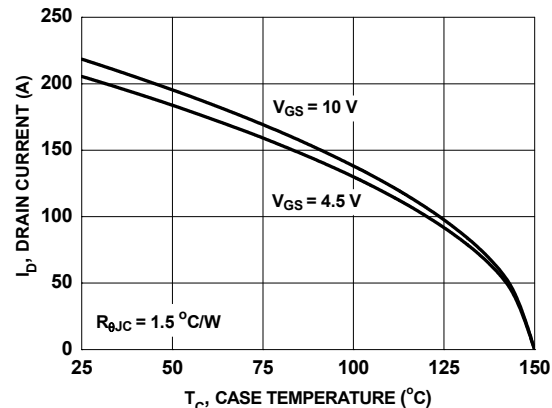


Figure 10. Maximum Continuous Drain Current vs Case Temperature

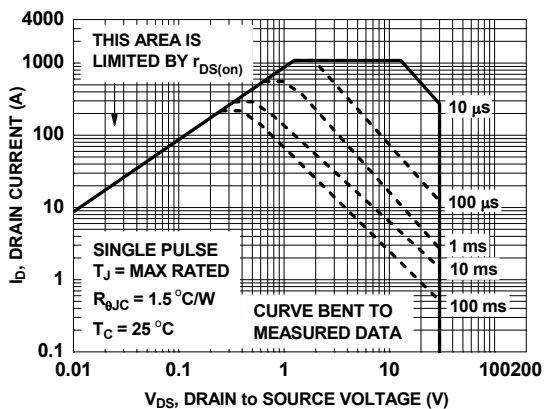


Figure 11. Forward Bias Safe Operating Area

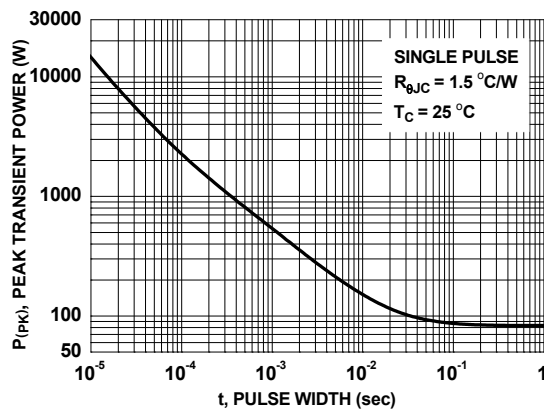


Figure 12. Single Pulse Maximum Power Dissipation

Typical Characteristics $T_J = 25\text{ }^{\circ}\text{C}$ unless otherwise noted.

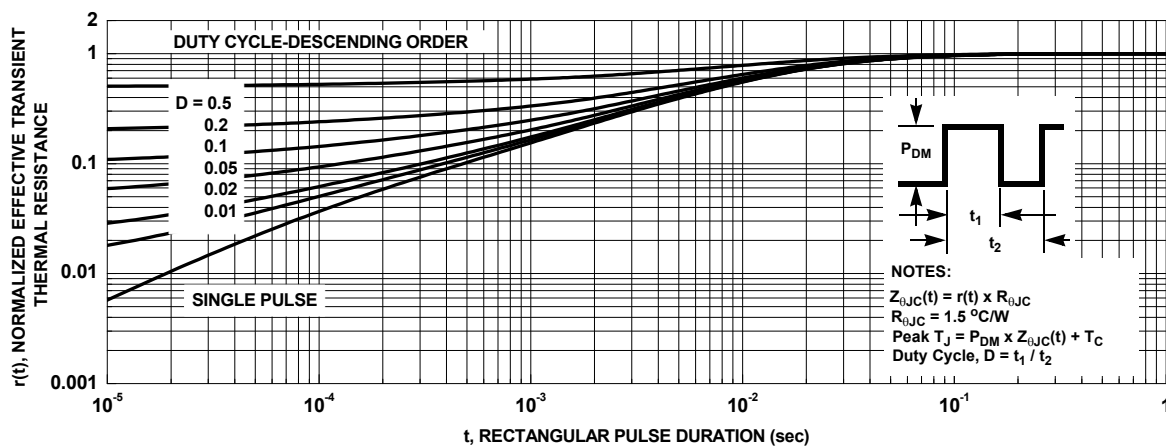
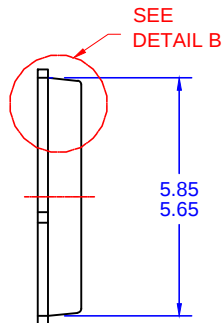


Figure 13. Junction-to-Case Transient Thermal Response Curve

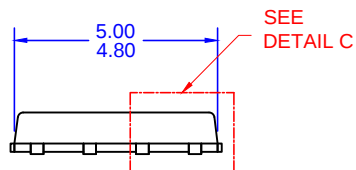
PQFN8 5X6, 1.27P
CASE 483AE
ISSUE A



TOP VIEW

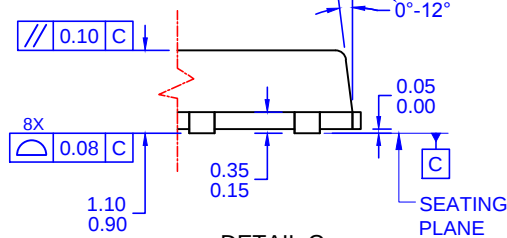


LAND PATTERN
RECOMMENDATION

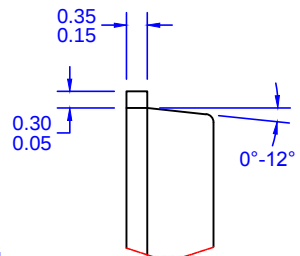


SIDE VIEW

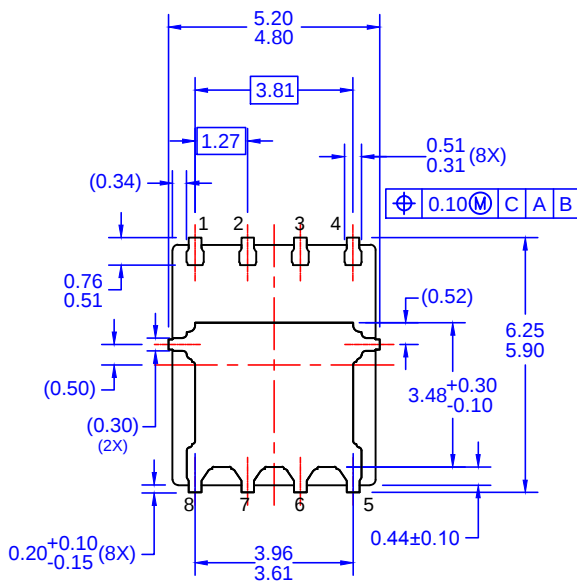
OPTIONAL DRAFT
ANGLE MAY APPEAR
ON FOUR SIDES
OF THE PACKAGE



DETAIL C
SCALE: 2:1



DETAIL B
SCALE: 2:1



BOTTOM VIEW

NOTES: UNLESS OTHERWISE SPECIFIED

- PACKAGE STANDARD REFERENCE: JEDEC MO-240, ISSUE A, VAR. AA.
- DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. MOLD FLASH OR BURRS DOES NOT EXCEED 0.10MM.
- ALL DIMENSIONS ARE IN MILLIMETERS.
- DIMENSIONING AND TOLERANCING PER ASME Y14.5M-2009.
- IT IS RECOMMENDED TO HAVE NO TRACES OR VIAS WITHIN THE KEEP OUT AREA.

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